



#### P-CHANNEL ENHANCEMENT MODE MOSFET PowerDI5060-8

## **Product Summary**

BV <sub>DSS</sub>	R <sub>DS(ON)</sub> Max	I <sub>D</sub> Max T <sub>C</sub> = +25°C
201/	$28m\Omega$ @ $V_{GS} = -10V$	-21A
-30V	38mΩ @ V <sub>GS</sub> = -4.5V	-18A

#### **Features and Benefits**

- Low R<sub>DS(ON)</sub> Minimizes On-State Losses
- Small Form Factor Thermally Efficient Package Enables Higher Density End Products
- 100% Unclamped Inductive Switching Ensures More Reliability
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- PPAP Capable (Note 4)

## **Description and Applications**

This MOSFET is designed to meet the stringent requirements of Automotive applications. It is qualified to AEC-Q101, supported by a PPAP and is ideal for use in:

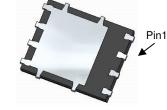
- Backlighting
- Power Management Functions
- DC-DC Converters

#### **Mechanical Data**

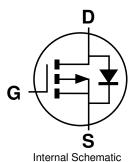
- Case: PowerDI5060-8
- Case Material: Molded Plastic, "Green" Molding Compound.
   UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections Indicator: See Diagram
- Terminals: Finish Matte Tin Annealed over Copper Leadframe.
   Solderable per MIL-STD-202, Method 208 <sup>3</sup>
- Weight: 0.097 grams (Approximate)

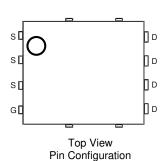


Top View



Bottom View





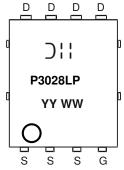
## Ordering Information (Note 5)

Part Number	Case	Packaging
DMP3028LPSQ-13	PowerDI5060-8	2,500/Tape & Reel

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- 2. See http://www.diodes.com/quality/lead\_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. Automotive products are AEC-Q101 qualified and are PPAP capable. Refer to https://www.diodes.com/quality/product-compliance-definitions/.
- 5. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/

## **Marking Information**



);; = Manufacturer's Marking
P3028LP = Product Type Marking Code
YYWW = Date Code Marking
YY = Year (ex: 17 = 2017)
WW = Week (01 to 53)



## **Maximum Ratings** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
Drain-Source Voltage	$V_{DSS}$	-30	V	
Gate-Source Voltage	$V_{GSS}$	±20	V	
Continuous Drain Current, V <sub>GS</sub> = -10V (Note 8)	$T_C = +25$ °C $T_C = +70$ °C	I <sub>D</sub>	-21 -17	А
Maximum Continuous Body Diode Forward Current (Note 8)	Is	-20	Α	
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)	I <sub>DM</sub>	-70	Α	
Pulsed Body Diode Forward Current (10µs Pulse, Duty Cycle	I <sub>SM</sub>	-70	Α	
Avalanche Current, L = 0.1mH (Note 9)	I <sub>AS</sub>	-21.4	Α	
Avalanche Energy, L = 0.1mH (Note 9)	E <sub>AS</sub>	22	mJ	

## **Thermal Characteristics**

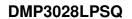
Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 6)		$P_D$	1.28	W
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	$R_{\theta JA}$	100	°C/W
Total Power Dissipation (Note 7)		P <sub>D</sub>	2.12	W
Thermal Resistance, Junction to Ambient (Note 7)	Steady State	$R_{\theta JA}$	60	°C/W
Total Power Dissipation (Note 8)		P <sub>D</sub>	35	W
Thermal Resistance, Junction to Case (Note 8)		$R_{ heta JC}$	3.0	°C/W
Operating and Storage Temperature Range		T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C

## **Electrical Characteristics** (T<sub>A</sub> = +25°C, unless otherwise specified.)

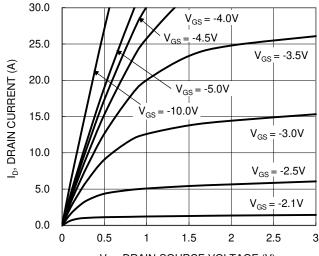
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 10)							
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	-30	_	_	V	$V_{GS} = 0V, I_D = -250\mu A$	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	_	_	-1	μA	$V_{DS} = -30V, V_{GS} = 0V$	
Gate-Source Leakage	Igss	_	_	±100	nA	$V_{GS} = \pm 20V$ , $V_{DS} = 0V$	
ON CHARACTERISTICS (Note 10)	ON CHARACTERISTICS (Note 10)						
Gate Threshold Voltage	V <sub>GS(TH)</sub>	-1.0	-1.3	-2.4	V	$V_{DS} = V_{GS}$ , $I_D = -250\mu A$	
Static Drain-Source On-Resistance	0	_	18	28	0	$V_{GS} = -10V, I_{D} = -7A$	
Static Drain-Source On-Resistance	R <sub>DS(ON)</sub>	_	28	38	mΩ	V <sub>GS</sub> = -4.5V, I <sub>D</sub> = -6.2A	
Diode Forward Voltage	$V_{SD}$	_	-0.7	-1.2	V	$V_{GS} = 0V, I_{S} = -2.1A$	
DYNAMIC CHARACTERISTICS (Note 11)	DYNAMIC CHARACTERISTICS (Note 11)						
Input Capacitance	C <sub>iss</sub>	1	1372	_	pF		
Output Capacitance	Coss		161	_	pF	$V_{DS} = -15V, V_{GS} = 0V,$ f = 1.0MHz	
Reverse Transfer Capacitance	$C_{rss}$	_	127	_	pF	T = 1.0IVIH2	
Gate Resistance	$R_g$	_	8.5	_	Ω	$V_{DS} = 0V, V_{GS} = 0V, f = 1.0MHz$	
Total Gate Charge (V <sub>GS</sub> = -4.5V)	Qg	_	11	_	nC		
Total Gate Charge (V <sub>GS</sub> = -10V)	Qg	_	22	_	nC		
Gate-Source Charge	Q <sub>gs</sub>	_	3.0	_	nC	$V_{DS} = -15V, I_{D} = -7A$	
Gate-Drain Charge	Q <sub>gd</sub>	-	3.7	_	nC	1	
Turn-On Delay Time	t <sub>D(ON)</sub>	-	4.8	_	ns		
Turn-On Rise Time	t <sub>R</sub>	_	5.5	_	ns	$V_{DD} = -15V, V_{GS} = -10V,$	
Turn-Off Delay Time	t <sub>D(OFF)</sub>	_	32.8	_	ns	$R_g = 6\Omega$ , $I_D = -7A$	
Turn-Off Fall Time	t <sub>F</sub>	_	17.74	_	ns		
Reverse Recovery Time	t <sub>RR</sub>	_	10.8	_	ns	74 11/11 4004/	
Reverse Recovery Charge	Q <sub>RR</sub>	_	3.4	_	nC	$I_S = -7A$ , $dI/dt = 100A/\mu s$	

6. Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
7. Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.
8. Thermal resistance from junction to soldering point (on the exposed drain pad). Notes:

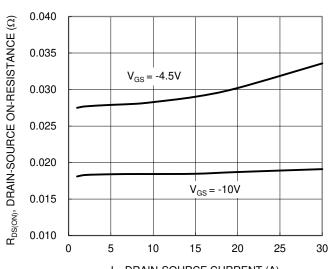
I. Is and E<sub>AS</sub> ratings are based on low frequency and duty cycles to keep T<sub>J</sub> = +25°C.
 Short duration pulse test used to minimize self-heating effect.
 Guaranteed by design. Not subject to product testing.







V<sub>DS</sub>, DRAIN-SOURCE VOLTAGE (V) Figure 1. Typical Output Characteristic



I<sub>D</sub>, DRAIN-SOURCE CURRENT (A) Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

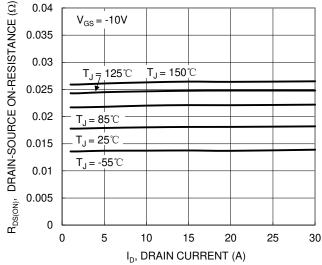


Figure 5. Typical On-Resistance vs. Drain Current and Temperature

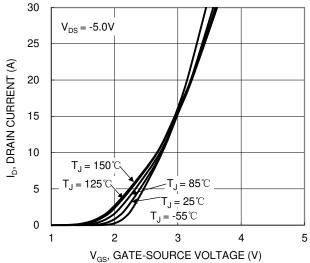


Figure 2. Typical Transfer Characteristic

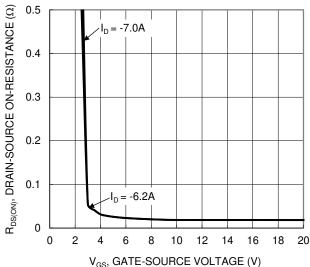


Figure 4. Typical Transfer Characteristic

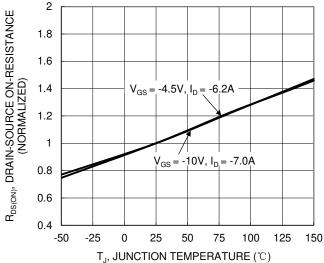


Figure 6. On-Resistance Variation with Temperature



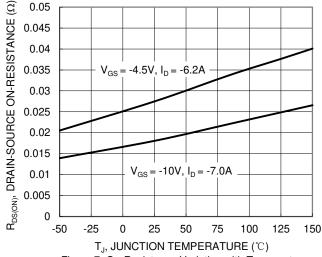
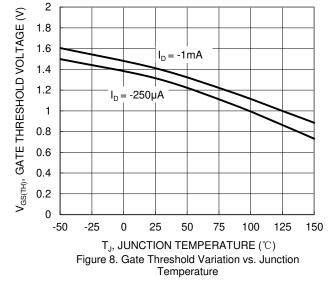
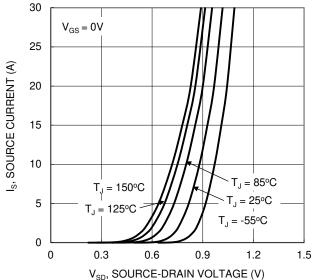
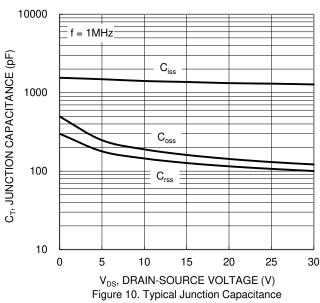


Figure 7. On-Resistance Variation with Temperature





V<sub>SD</sub>, SOURCE-DRAIN VOLTAGE (V) Figure 9. Diode Forward Voltage vs. Current



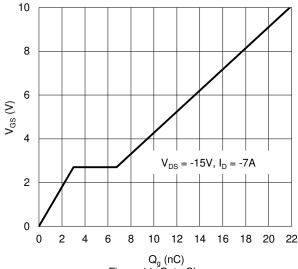


Figure 11. Gate Charge

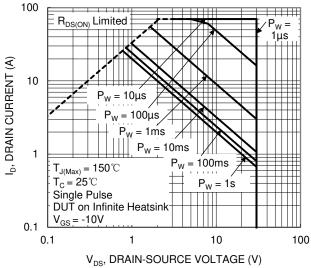


Figure 12. SOA, Safe Operation Area



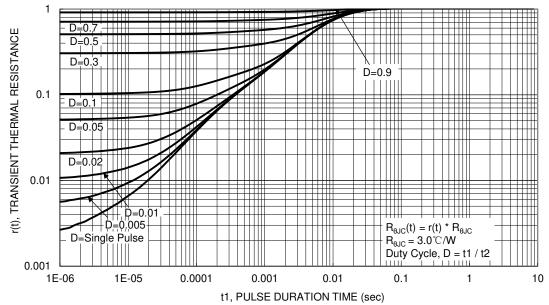


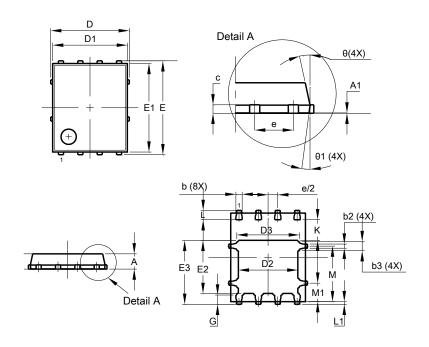
Figure 13. Transient Thermal Resistance



## **Package Outline Dimensions**

Please see http://www.diodes.com/package-outlines.html for the latest version.

#### PowerDI5060-8

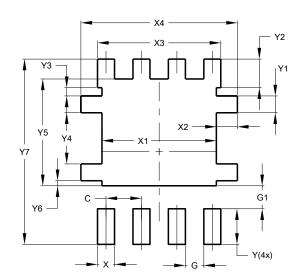


PowerDI5060-8					
Dim	Min	Max	Тур		
Α	0.90	1.10	1.00		
A1	0.00	0.05	-		
b	0.33	0.51	0.41		
b2	0.200	0.350	0.273		
b3	0.40	0.80	0.60		
С	0.230	0.330	0.277		
D	ļ	5.15 BSC	;		
D1	4.70	5.10	4.90		
D2	3.70	4.10	3.90		
D3	3.90	4.30	4.10		
Е	(	6.15 BSC	;		
E1	5.60	6.00	5.80		
E2	3.28	3.68	3.48		
E3	3.99	4.39	4.19		
е	1.27 BSC				
G	0.51	0.71	0.61		
K	0.51	-	-		
L	0.51	0.71	0.61		
L1	0.100	0.200	0.175		
М	3.235	4.035	3.635		
M1	1.00	1.40	1.21		
Θ	10°	12°	11°		
Θ1	6°	8°	7°		
All Dimensions in mm					

# **Suggested Pad Layout**

Please see http://www.diodes.com/package-outlines.html for the latest version.

### PowerDI5060-8



Dimensions	Value (in mm)				
С	1.270				
G	0.660				
G1	0.820				
Х	0.610				
X1	4.100				
X2	0.755				
Х3	4.420				
X4	5.610				
Υ	1.270				
Y1	0.600				
Y2	1.020				
Y3	0.295				
Y4	1.825				
Y5	3.810				
Y6	0.180				
<b>Y</b> 7	6.610				



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